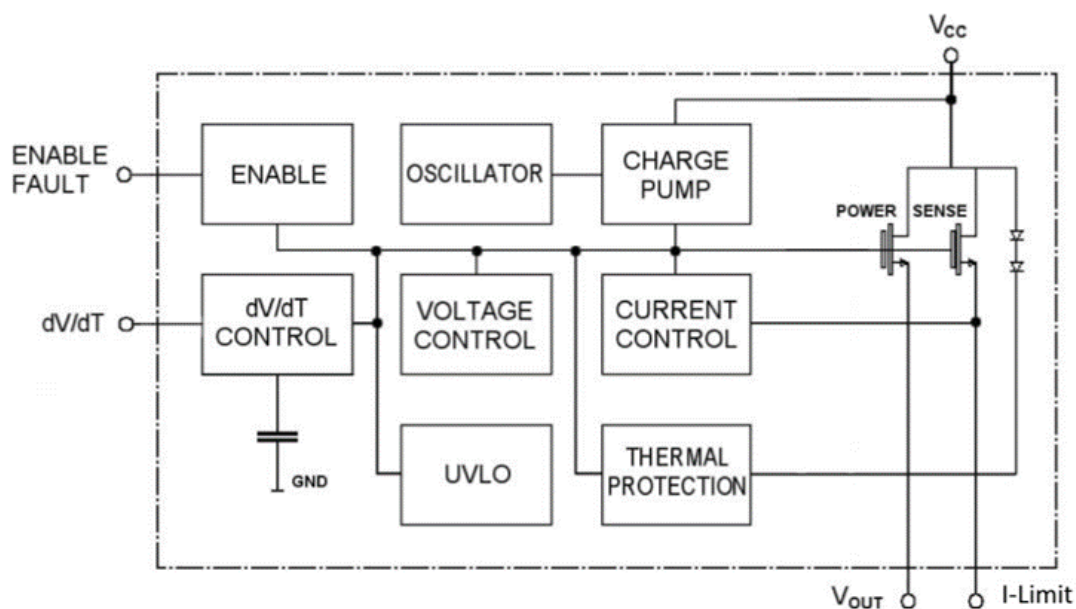


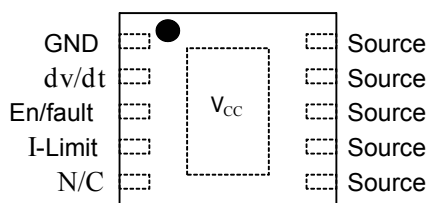
1 Device block diagram

Figure 1. Block diagram



2 Pin configuration

Figure 2. Pin configuration (top view)



AMG300320171101MT

Table 1. Pin description

Pin n°	Symbol	Note
1	GND	Ground pin.
2	dv/dt	The internal dv/dt circuit controls the slew rate of the output voltage on turn-on. The internal capacitor allows a ramp-up time of around 1 ms. An external capacitor can be added to this pin to increase the ramp time. If an additional capacitor is not required, this pin should be left open.
3	En/fault	The Enable/Fault pin is a tri-state, bi-directional interface. During normal operation the pin must be left floating, or it can be used to disable the output of the device by pulling it to ground using an open drain or open collector device. If a thermal fault occurs, the voltage on this pin goes into an intermediate state to signal a monitor circuit that the device is in thermal shutdown. It can be connected to another device of this family to cause a simultaneous shutdown during thermal events.
4	I-Limit	A resistor between this pin and the Source pin sets the overload and short-circuit current limit levels.
5	N/C	Not connected.
6 to 10	V _{OUT} /Source	Connected to the source of the internal power MOSFET and to the output terminal of the fuse.
11	V _{CC}	Exposed pad. Positive input voltage must be connected to V _{CC} .

3 Maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	Positive power supply voltage (steady-state)	-0.3 to 18	V
	Positive power supply voltage (max. 100 ms)	-0.3 to 25	
V _{OUT/source}	(max. 100 ms)	-0.3 to V _{CC} +0.3	V
I-Limit	(max. 100 ms)	-0.3 to 25	V
En/fault		-0.3 to 7	V
dv/dt		-0.3 to 7	V
T _{op}	Operating junction temperature range	-40 to 125	°C
T _{STG}	Storage temperature range	-65 to 150	°C
T _{LEAD}	Lead temperature (soldering) 10 s	260	°C

- The thermal limit is set above the maximum thermal ratings. It is not recommended to operate the device at temperatures greater than the maximum ratings for extended periods of time.

Note: Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJA}	Thermal resistance junction-ambient	52.7	°C/W
R _{thJC}	Thermal resistance junction-case	17.4	°C/W

- The value refers to the package mounted on a 4 layer JEDEC standard test board with 4 thermal vias connecting the thermal land to the first buried plane.

Table 4. ESD performance

Symbol	Parameter	Test condition	Value	Unit
ESD	ESD protection	HBM	2	kV
		MM	200	V
		CDM	500	V

4 Electrical characteristics

$V_{CC} = 12\text{ V}$, $V_{EN} = 3.3\text{ V}$, $C_I = 10\text{ }\mu\text{F}$, $C_O = 47\text{ }\mu\text{F}$, $T_J = 25\text{ }^\circ\text{C}$ (unless otherwise specified).

Table 5. Electrical characteristics for STEF12E

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Under/overvoltage protection						
V_{Clamp}	Output clamping voltage	$V_{CC} = 18\text{ V}$	13.8	15	16.2	V
V_{UVLO}	Undervoltage lockout	Turn-on, voltage rising	7.7	8.5	9.3	V
V_{Hyst}	UVLO hysteresis			0.80		V
Power MOSFET						
t_{dly}	Delay time	Enabling of chip to $I_D = 100\text{ mA}$ with a 1 A resistive load		350		μs
R_{DSon}	On-resistance ⁽¹⁾	$-40\text{ }^\circ\text{C} < T_J < 125\text{ }^\circ\text{C}$ ⁽²⁾	35	45	55	$\text{m}\Omega$
V_{OFF}	Off-state output voltage	$V_{CC} = 18\text{ V}$, $V_{GS} = 0$, $R_L = \text{infinite}$		40	100	mV
I_D	Continuous current	0.5 in ² pad, $T_A = 25\text{ }^\circ\text{C}$ ⁽²⁾		3.6		A
		Minimum copper, $T_A = 80\text{ }^\circ\text{C}$		1.7		
Current limit						
I_{Short}	Short-circuit current limit	$R_{Limit} = 22\text{ }\Omega$	3.3	4.4	5.5	A
I_{Lim}	Overload current limit	$R_{Limit} = 22\text{ }\Omega$		4.4		A
dv/dt circuit						
dv/dt	Output voltage ramp time	Enable to $V_{OUT} = 11.7\text{ V}$, No $C_{dv/dt}$	0.5	0.9	2.6	ms
Enable/fault						
V_{IL}	Low level input voltage	Output disabled	0.35	0.58	0.81	V
$V_{I(INT)}$	Intermediate level input voltage	Thermal fault, output disabled	0.82	1.4	1.95	V
V_{IH}	High level input voltage	Output enabled	1.96	2.64	3.3	V
$V_{I(MAX)}$	High state maximum voltage		3.4	4.3	5.4	V
I_{IL}	Low level input current (sink)	$V_{Enable} = 0\text{ V}$		-10	-30	μA
I_I	High level leakage current for external switch	$V_{Enable} = 3.3\text{ V}$			1	μA
	Maximum fan-out for fault signal	Total numbers of chips that can be connected to this pin for simultaneous shutdown			3	Units
Total device						
I_{Bias}	Bias current	Device operational		1.5	2	mA
		Thermal shutdown		1		
V_{min}	Minimum operating voltage				7.6	V
Thermal latch						
TSD	Shutdown temperature	⁽¹⁾		165		$^\circ\text{C}$

1. Pulse test: pulse width = 300 μs , duty cycle = 2%.

2. Guaranteed by design, but not tested in production.

5 Typical application

Figure 3. Application circuit

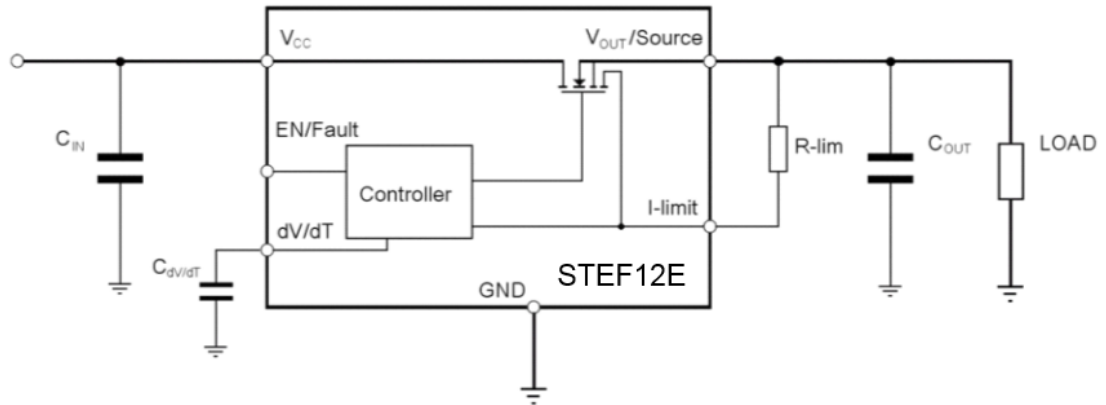
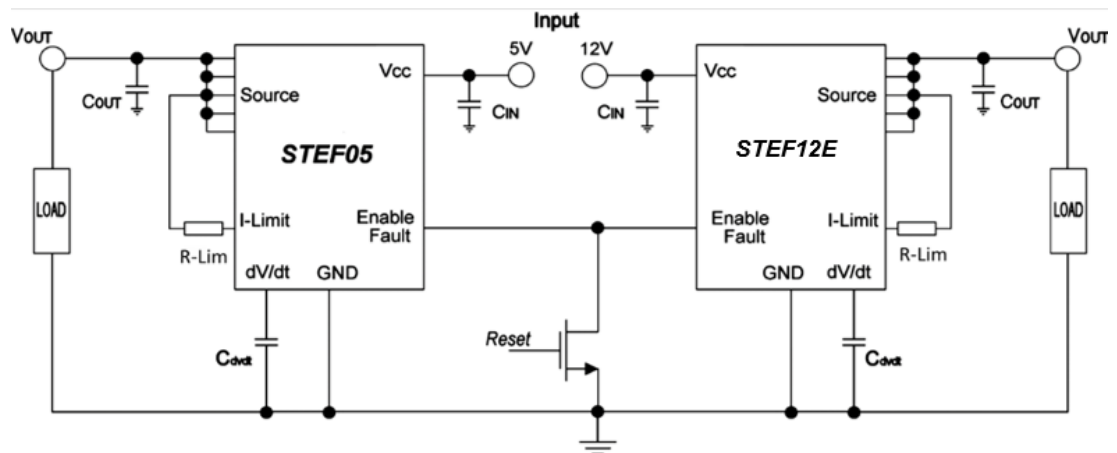


Figure 4. Typical HDD application circuit



6 Operating modes

6.1 Turn-on

When the input voltage is applied, the enable/fault pin goes up to the high state, enabling the internal control circuitry.

After an initial delay time of typically 350 μ s, the output voltage is supplied with a slope defined by the internal dv/dt circuitry. If no additional capacitor is connected to dv/dt pin, the total time, from the enable signal going high to the output voltage reaching the nominal value, is around 1 ms (refer to [Figure 5. Delay time and \$V_{OUT}\$ ramp-up time](#)).

6.2 Normal operating conditions

The STEF12E E-Fuse behaves like a mechanical fuse, buffering the circuitry on its output with the same voltage shown on its input, with a small voltage fall due to the N-channel MOSFET $R_{DS(on)}$.

6.3 Output voltage clamp

This internal protection circuit clamps the output voltage to a maximum safe value, typically 15 V, if the input voltage exceeds this threshold.

6.4 Current limiting

When an overload event occurs, the current limiting circuit reduces the conductivity of the power MOSFET, in order to clamp the output current at the value selected externally by the limiting resistor R_{Limit} (see [Figure 3. Application circuit](#)).

6.5 Thermal shutdown

If the device temperature exceeds the thermal latch threshold, typically 165 $^{\circ}$ C, the thermal shutdown circuitry turns the power MOSFET off, thus disconnecting the load. The EN/fault pin of the device is automatically set to an intermediate voltage, in order to signal the overtemperature event. In this condition the E-Fuse can be reset either by cycling the supply voltage or by pulling down the EN pin below the V_{IL} threshold and then releasing it.

6.6 R-Lim calculation

As shown in [Figure 3. Application circuit](#), the device uses an internal N-channel SenseFET with a fixed ratio, to monitor the output current and limit it at the level set by the user.

To achieve the requested current limitation, the R-Lim value can be estimated by using the following theoretical formula, together with the graph in [Figure 13. Current limit vs. \$R_{Limit}\$](#) .

$$R_{Lim} = \frac{95}{I_{Short}} \quad (1)$$

6.7 $C_{dv/dt}$ calculation

Connecting a capacitor between the $C_{dv/dt}$ pin and GND allows the modification of the output voltage ramp-up time.

Given the desired time interval Δt , during which the output voltage goes from zero to its maximum value, the capacitance to be added to the $C_{dv/dt}$ pin can be calculated using the following theoretical formula:

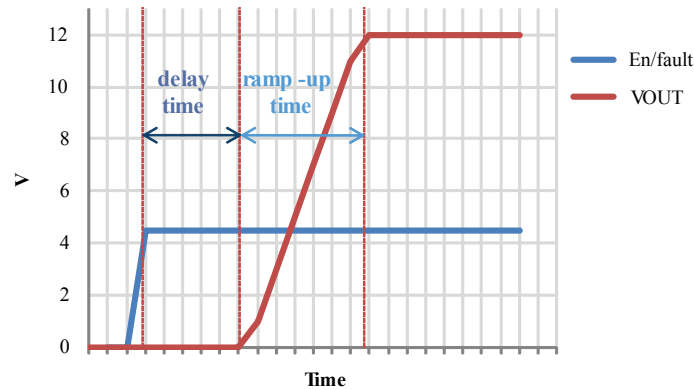
$$C_{dv/dt} = 3.92 \times 10^{-8} \Delta t - 35.3 \times 10^{-12} \quad (2)$$

Where $C_{dv/dt}$ is expressed in farads and the time in seconds.

The addition of an external $C_{dv/dt}$ also influences the initial delay time, defined as the time between the enable signal going high and the start of the V_{OUT} slope ([Figure 5. Delay time and \$V_{OUT}\$ ramp-up time](#)).

The contribution of the external capacitor to this time interval can be estimated by using the following theoretical formula:

$$\text{delay time [s]} = 35 \times 10^{-5} + 71 \times 10^5 \times C_{dv/dt} [F] \quad (3)$$

Figure 5. Delay time and V_{OUT} ramp-up time


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6.8 En/fault pin

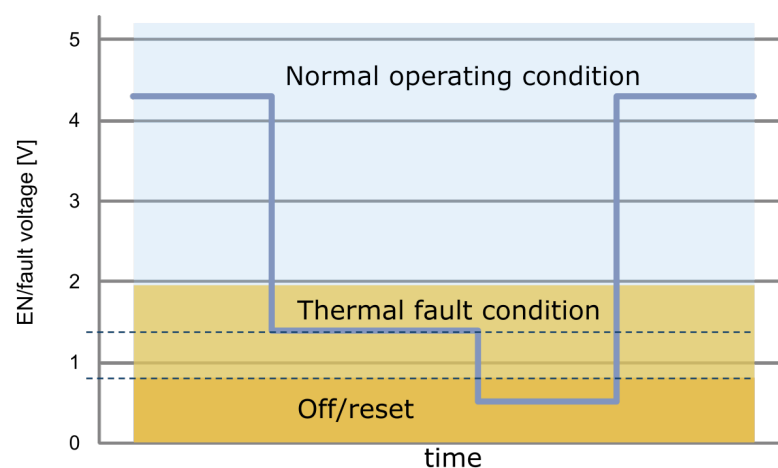
The En/fault pin has the dual function to control the output of the device and, at the same time, provide the application with information about the device status.

When it is used as a standard enable pin, it should be connected to an external open-drain or open-collector device. In this case, when it is pulled to low logic level, it turns the output of the E-Fuse off.

If this pin is left floating, since it has an internal pull-up circuitry, the output of the E-Fuse is kept on, in normal operating conditions.

In case of thermal fault, the pin is pulled to an intermediate state (Figure 6. En/fault pin status). This signal can be provided to a monitor circuit, informing it that a thermal shutdown has occurred, or it can be directly connected to the Enable/fault pin of the other STEFxx devices on the same application in order to achieve a simultaneous enable/disable feature.

When a thermal fault occurs, the device can be reset either by cycling the supply voltage or by pulling down the Enable pin below the V_{IL} threshold and then releasing it.

Figure 6. En/fault pin status


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7 Typical performance characteristics

The following plots are referred to the typical application circuit and, unless otherwise noted, at $T_A = 25\text{ }^{\circ}\text{C}$.

Figure 7. Clamping voltage vs. temperature

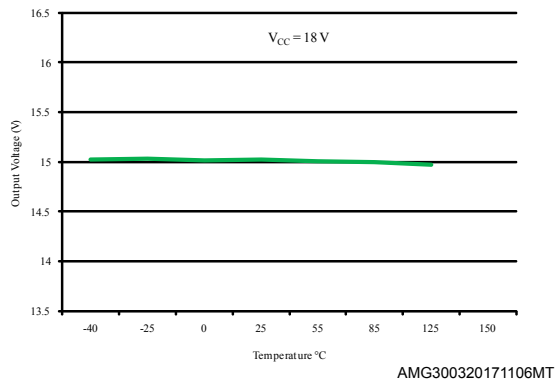


Figure 8. UVLO voltage vs. temperature

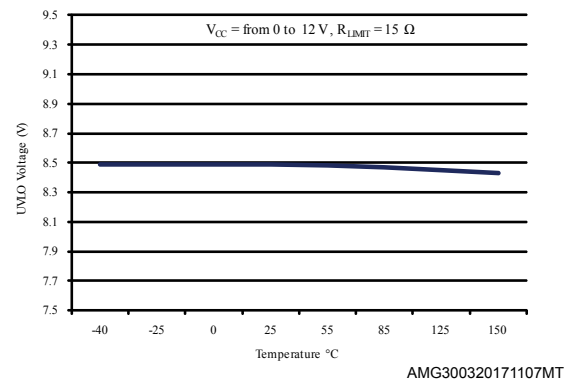


Figure 9. UVLO hysteresis vs. temperature

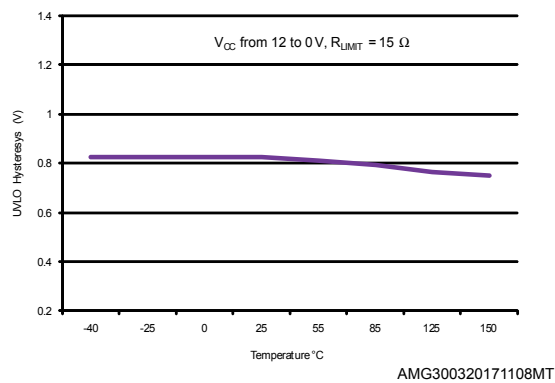


Figure 10. Off-state voltage vs. temperature

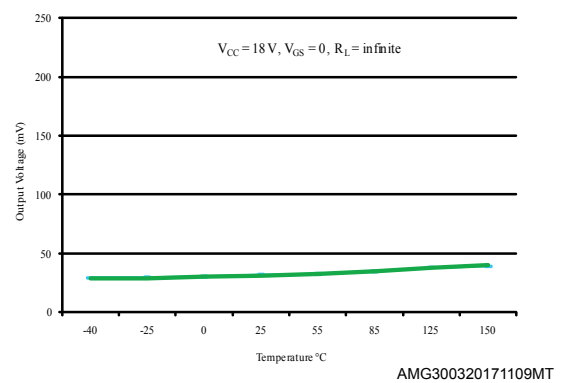


Figure 11. Bias current (device operational)

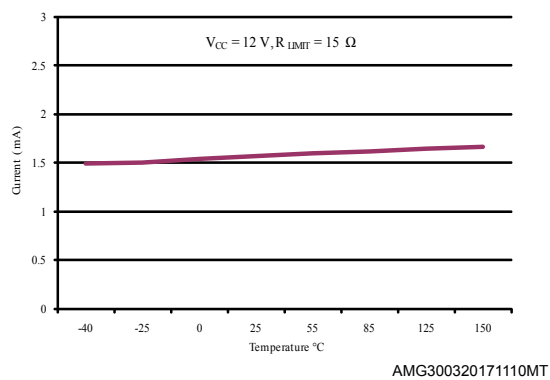


Figure 12. ON-resistance vs. temperature

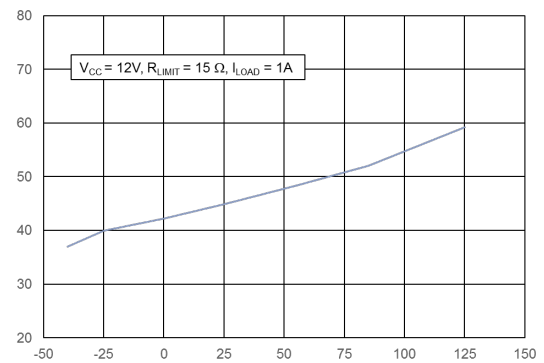
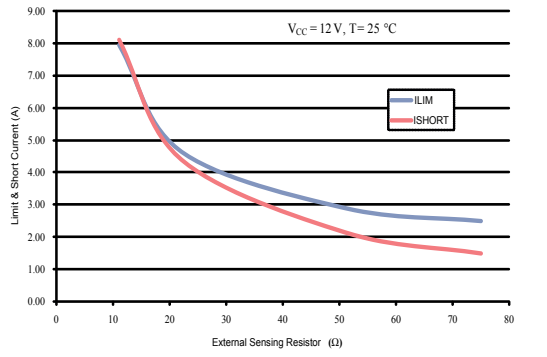
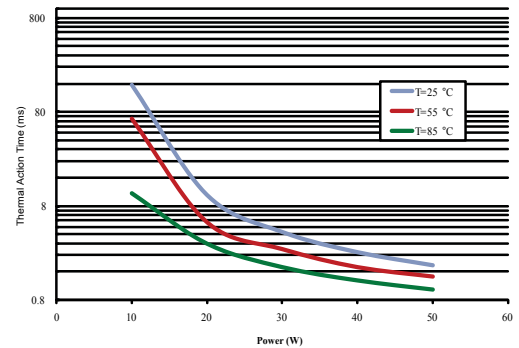
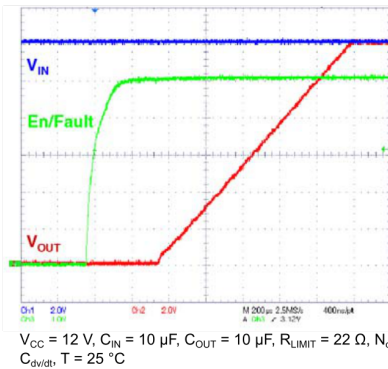


Figure 13. Current limit vs. R_{LIMIT}


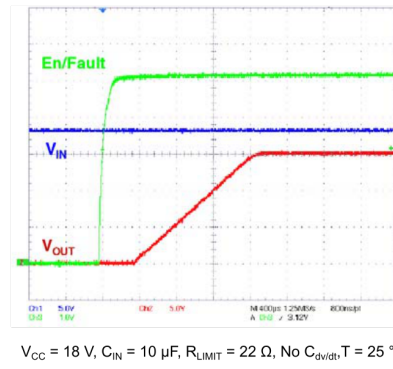
AMG300320171112MT

Figure 14. Thermal latch delay vs. power


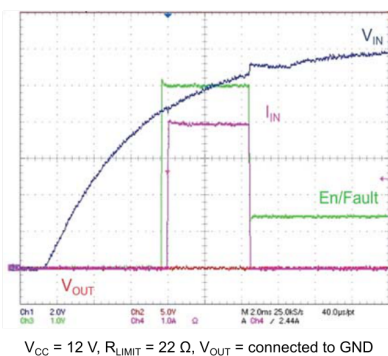
AMG300320171113MT

Figure 15. V_{OUT} ramp-up vs. enable


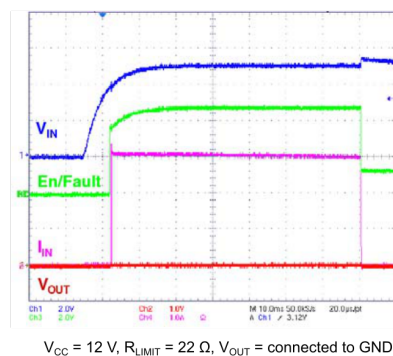
AMG300320171114MT

Figure 16. V_{OUT} clamping


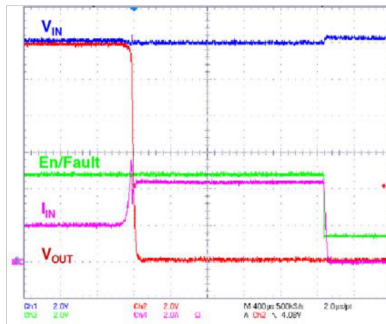
AMG300320171115MT

Figure 17. Line transient


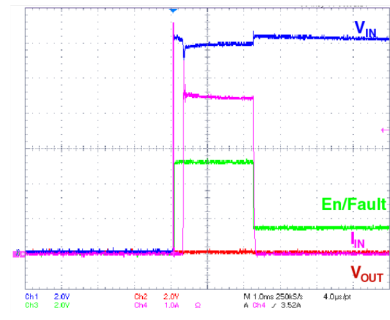
AMG300320171116MT

Figure 18. Startup into output short-circuit


AMG300320171117MT

Figure 19. Thermal latch from 2 A load to short-circuit


AMG300320171118MT

Figure 20. Startup into output short-circuit (fast rise)

 $V_{CC} = 12\text{ V}$, $R_{LIMIT} = 22\ \Omega$, V_{OUT} = connected to GND

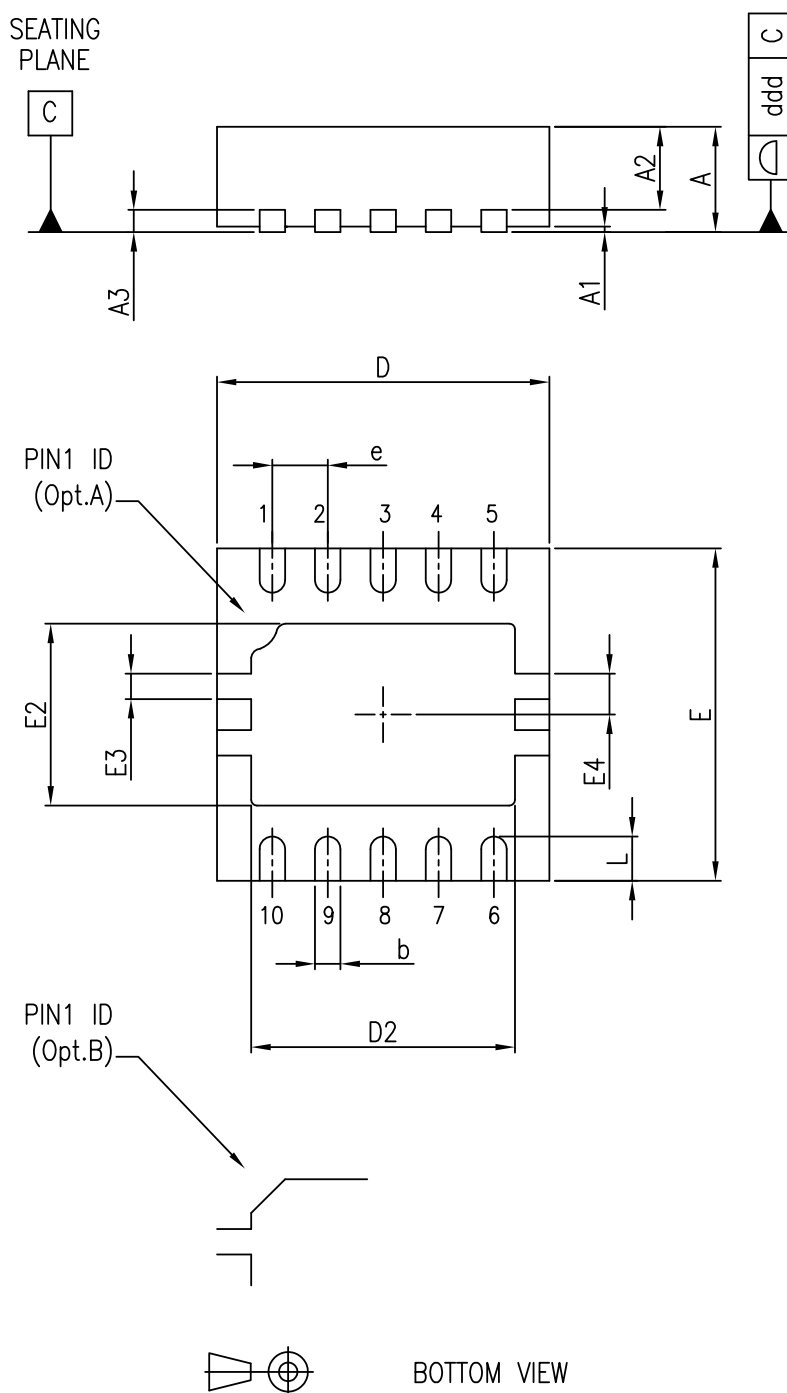
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8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

8.1 DFN10 (3x3 mm) package information

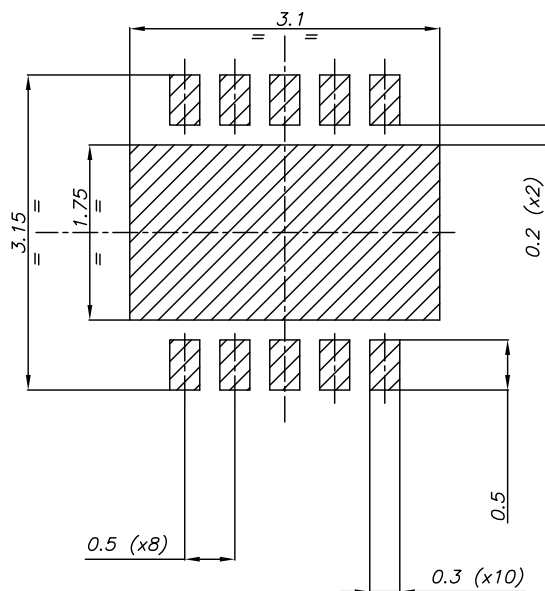
Figure 21. DFN10 (3x3 mm) package outline



7426335_L

Table 6. DFN10 (3x3 mm) mechanical data

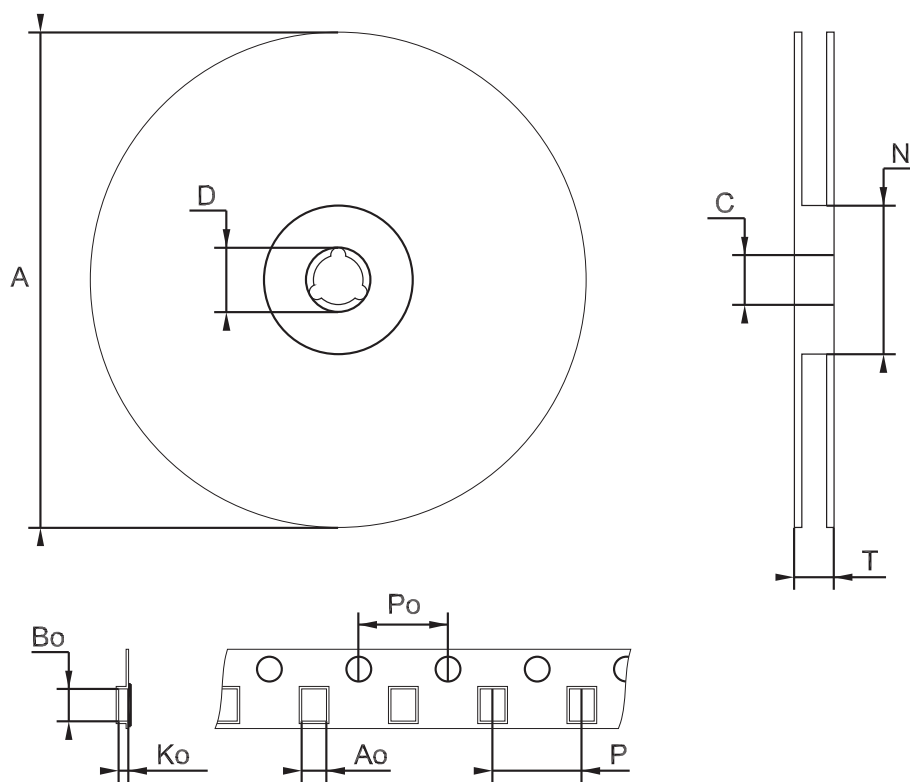
Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1		0.02	0.05
A2		0.70	
A3		0.20	
b	0.18	0.23	0.30
D	2.85	3.00	3.15
D2	2.23	2.38	2.50
E	2.85	3.00	3.15
E2	1.49	1.64	1.75
E3	0.230		
E4	0.365		
e		0.50	
L	0.30	0.40	0.50
ddd			0.08

Figure 22. DFN10 (3x3 mm) recommended footprint


7426335_L

8.2 DFN10 (3 x 3 mm) package information

Figure 23. DFN10 (3x3 mm) tape and reel outline



Note: Drawing not in scale

Table 7. DFN10 (3x3 mm) tape and reel mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			330
C	12.8		13.2
D	20.2		
N	60		
T			18.4
Ao		3.3	
Bo		3.3	
Ko		1.1	
Po		4	
P		8	

Revision history

Table 8. Document revision history

Date	Revision	Changes
30-Oct-2018	1	Initial release.

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